

Characterization of the n-in-p CiS pixel production

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We present the results of the pre-irradiation characterization of the n-in-p pixel production, performed at CiS in the framework of the RD50 Collaboration, containing sensors designed both for the ATLAS and the CMS pixel upgrade R&D activities.

A comparison of the performance of the ATLAS pixel sensors with standard and reduced guard ring will be given. The tuning of the TCAD simulation, obtained with diode structures of this production will be shown. The quality and the effect of the post-processing needed for the creation of the Under Bump Metallization will be discussed.

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